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SEMICONDUCTOR®

November 2013

FQD13N06 — N-Channel QFET[®] MOSFET

FQD13N06 N-Channel QFET® MOSFET

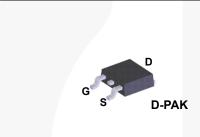
60 V, 10 A, 140 mΩ

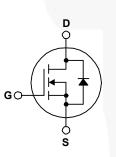
Description

This N-Channel enhancement mode power MOSFET is • 10 A, 60 V, $R_{DS(on)}$ = 140 m Ω (Max.) @ V_{GS} = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state $I_D = 5.0 \text{ A}$ Low Gate Charge (Typ. 5.8 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 15 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- $I_{D} = 5.0 \text{ A}$





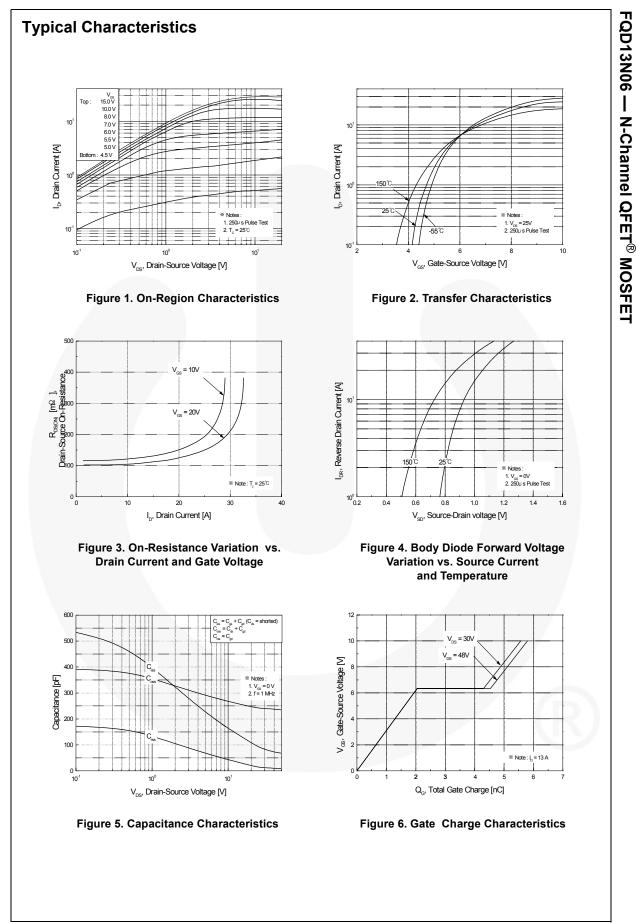
Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

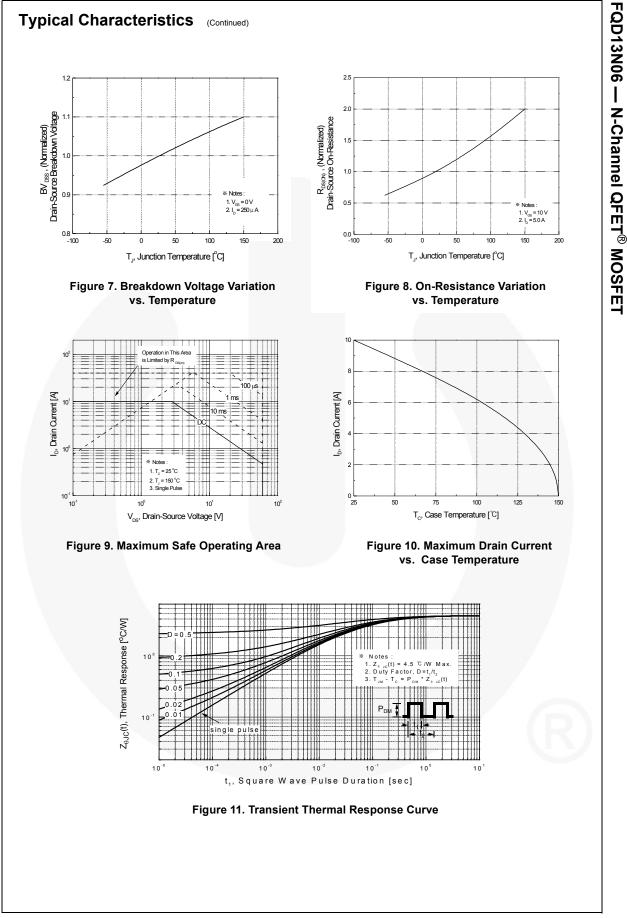
Symbol	Parameter		FQD13N06TM	Unit
V _{DSS}	Drain-Source Voltage		60	V
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$)		10	A
	- Continuous (T _C = 100°C)		6.3	A
I _{DM}	Drain Current - Pulsed	(Note 1)	40	A
V _{GSS}	Gate-Source Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	85	mJ
I _{AR}	Avalanche Current	(Note 1)	10	A
E _{AR}	Repetitive Avalanche Energy	(Note 1)	2.8	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	7.0	V/ns
P _D	Power Dissipation (T _A = 25°C) *		2.5	W
	Power Dissipation (T _C = 25°C)		28	W
	- Derate above 25°C		0.22	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
Τ _L	Maximum lead temperature for soldering, 1/8" from case for 5 seconds		300	°C

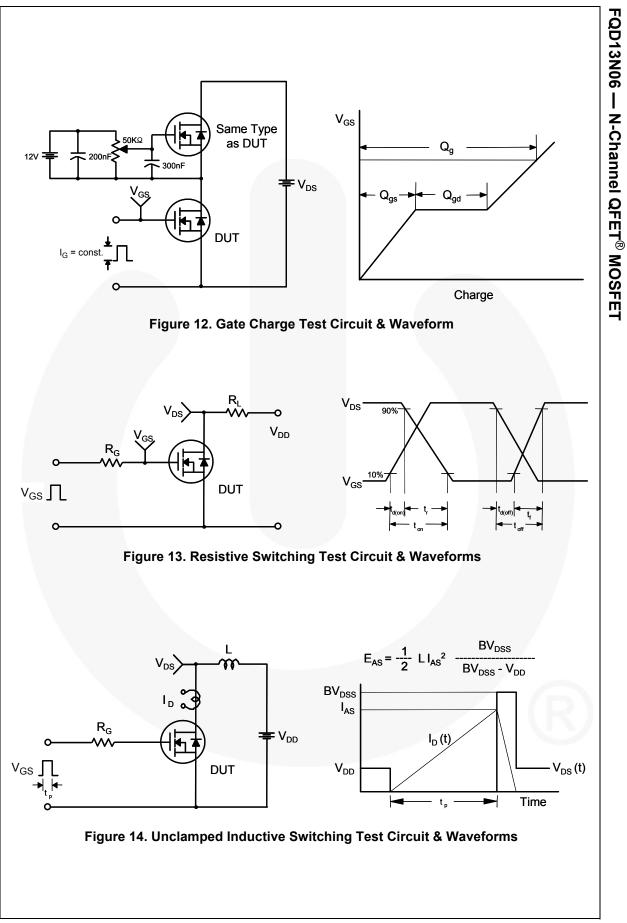
Thermal Characteristics

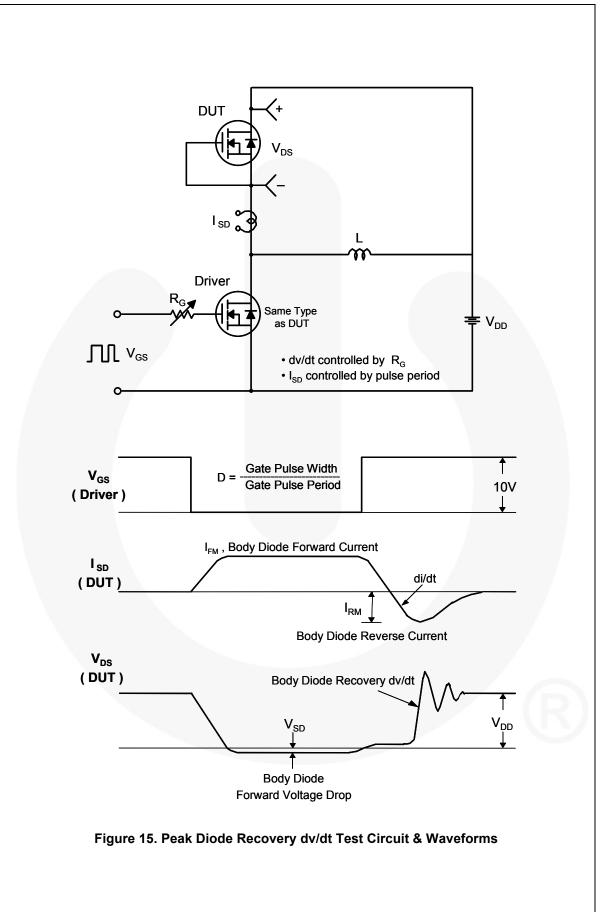
Symbol	Parameter	FQD13N06TM	Unit
R_{\thetaJC}	Thermal Resistance, Junction to Case, Max.	4.5	
Р	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	°C/W
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	50	

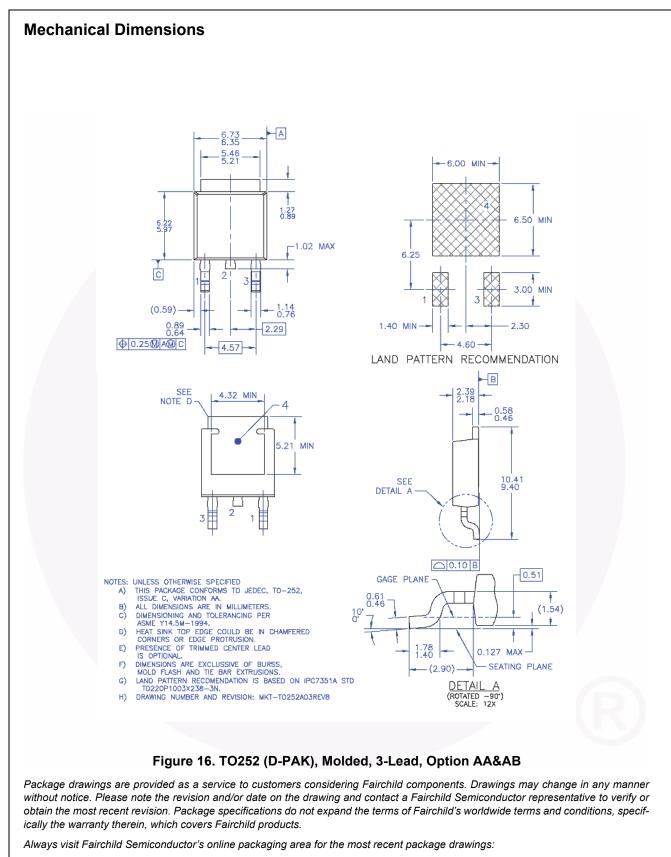
r acterist Drain-Sou	Parameter		PAK C unless oth	Tape and Ree	I 330) mm	16 n	am	
r acterist Drain-Sou Breakdow	Parameter iCS	T _C = 25°0	1						2500 unit
r acterist Drain-Sou Breakdow	Parameter iCS		1	erwise noted					
Drain-Sou Breakdow				Test Conditions		Min.	Тур.	Max.	Unit
Drain-Sou Breakdow									
		е	V _{GS} = (V, I _D = 250 μA		60			V
	n Voltage Temperature t	e	I _D = 250 25°C) μA, Referenced	to		0.06		V/°C
Zero Gate Voltage Drain Current		V _{DS} = 60 V, V _{GS} = 0 V					1	μA	
Zero Gale	Voltage Drain Current	L	-	8 V, T _C = 125°C				10	μΑ
Gate-Body	/ Leakage Current, Fo	rward		25 V, V _{DS} = 0 V				100	nA
Gate-Body	/ Leakage Current, Re	everse	V _{GS} = -	25 V, V _{DS} = 0 V				-100	nA
racterist	ics								
Gate Thre	shold Voltage		V _{DS} = \	/ _{GS} , I _D = 250 μA		2.0		4.0	V
Static Dra	n-Source On-Resistar	nce	V _{GS} = 1	0 V, I _D = 5.0 A			0.11	0.14	Ω
Forward T	ransconductance		V _{DS} = 2	5 V, I _D = 5.0 A			4.9		S
c Charac	teristics								
		-	$V_{} = 25 V V_{} = 0 V$			240	310	pF	
Output Ca	pacitance					-	90	120	pF
Reverse T	ransfer Capacitance						15	20	pF
a Chara	otoriotico								
-									
Turn-On D	ecteristics	-					5	20	ns
Turn-On E	elay Time			0 V, I _D = 6.5 A,			5	20	ns
Turn-On F	elay Time Rise Time	_	V _{DD} = 3 R _G = 28	-			25	60	ns
Turn-On F Turn-Off D	elay Time Rise Time Delay Time	1		-	(Note 4)		25 8		ns
Turn-On F Turn-Off D Turn-Off F	velay Time Rise Time Delay Time all Time		R _G = 25	δΩ	(Note 4)		25	60 25	ns
Turn-On F Turn-Off D Turn-Off F Total Gate	velay Time Rise Time Delay Time all Time		R _G = 28	5 Ω 8 V, I _D = 13 A,	(Note 4)		25 8 15	60 25 40	ns ns ns
Turn-On F Turn-Off D Turn-Off F Total Gate	velay Time kise Time velay Time all Time Charge rce Charge		R _G = 25	5 Ω 8 V, I _D = 13 A,	(Note 4)	 	25 8 15 5.8	60 25 40	ns ns ns nC
Turn-On F Turn-Off D Turn-Off F Total Gate Gate-Sour Gate-Drain	velay Time tise Time elay Time all Time Charge rce Charge n Charge		R _G = 25 V _{DS} = 4 V _{GS} = 1	5 Ω 8 V, I _D = 13 A, 0 V	(Note 4)	 	25 8 15 5.8 2.0	60 25 40 7.5 	ns ns ns nC nC
Turn-On F Turn-Off D Turn-Off F Total Gate Gate-Soun Gate-Drain	Velay Time Nelay Time All Time Charge The Charge The Charge Charge Charge		$R_G = 25$ $V_{DS} = 4$ $V_{GS} = 1$ and Max	5 Ω 8 V, I _D = 13 A, 0 V imum Ratings	(Note 4)	 	25 8 15 5.8 2.0 2.5	60 25 40 7.5 	ns ns nC nC nC
Turn-On F Turn-Off D Turn-Off F Total Gate Gate-Sour Gate-Drain Durce Di Maximum	Velay Time Nelay Time Nelay Time all Time Charge Charge In Charge Ode Characterist Continuous Drain-Sou	urce Dio	$R_{G} = 25$ $V_{DS} = 4$ $V_{GS} = 1$ $M Max$ ode Forwa	S Ω 8 V, I _D = 13 A, 0 V imum Ratings ard Current	(Note 4)	 	25 8 15 5.8 2.0 2.5	60 25 40 7.5 10	ns ns nC nC nC A
Turn-On F Turn-Off D Turn-Off F Total Gate Gate-Soun Gate-Drain Durce Di Maximum Maximum	Velay Time Velay Time Velay Time all Time Charge Charge Charge Ode Characterist Continuous Drain-Sou Pulsed Drain-Source I	urce Dio Diode F	$R_{G} = 25$ $V_{DS} = 4$ $V_{GS} = 1$ Max $V_{GS} = 1$	S Ω $8 V, I_D = 13 A,$ 0 V imum Ratings ard Current urrent	(Note 4)	 	25 8 15 5.8 2.0 2.5	60 25 40 7.5 10 40	ns ns nC nC nC A A
Turn-On F Turn-Off D Turn-Off F Total Gate Gate-Sour Gate-Drain Ource Di Maximum Maximum Drain-Sou	Velay Time Nelay Time Nelay Time all Time Charge Charge In Charge Ode Characterist Continuous Drain-Sou	urce Dio Diode F	$R_{G} = 25$ $V_{DS} = 4$ $V_{GS} = 1$ $M d Max$ $Torward C$ $V_{GS} = 0$	S Ω 8 V, I _D = 13 A, 0 V imum Ratings ard Current	(Note 4)	 	25 8 15 5.8 2.0 2.5	60 25 40 7.5 10	ns ns nC nC nC A
	Gate-Body racteristi Gate Three Static Drai Forward Th c Charac Input Capa Output Ca Reverse T	Gate-Body Leakage Current, Re racteristics Gate Threshold Voltage	Gate-Body Leakage Current, Reverse racteristics Gate Threshold Voltage Static Drain-Source On-Resistance Forward Transconductance c Characteristics Input Capacitance Output Capacitance	Gate-Body Leakage Current, Reverse $V_{GS} = -$ racteristics $V_{DS} = V_{DS} = V_{DS}$ Gate Threshold Voltage $V_{DS} = V_{DS} = V_{DS}$ Static Drain-Source On-Resistance $V_{GS} = 1$ Forward Transconductance $V_{DS} = 2$ c Characteristics Input Capacitance Output Capacitance $V_{DS} = 2$	Gate-Body Leakage Current, Reverse $V_{GS} = -25 \text{ V}, V_{DS} = 0 \text{ V}$ racteristicsGate Threshold Voltage $V_{DS} = V_{GS}, I_D = 250 \mu \text{A}$ Static Drain-Source On-Resistance $V_{GS} = 10 \text{ V}, I_D = 5.0 \text{ A}$ Forward Transconductance $V_{DS} = 25 \text{ V}, I_D = 5.0 \text{ A}$ C CharacteristicsInput Capacitance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1.0 \text{ MHz}$ Reverse Transfer Capacitance	Gate-Body Leakage Current, Reverse $V_{GS} = -25 \text{ V}, V_{DS} = 0 \text{ V}$ racteristicsGate Threshold Voltage $V_{DS} = V_{GS}, I_D = 250 \mu \text{A}$ Static Drain-Source On-Resistance $V_{GS} = 10 \text{ V}, I_D = 5.0 \text{ A}$ Forward Transconductance $V_{DS} = 25 \text{ V}, I_D = 5.0 \text{ A}$ c Characteristics Input CapacitanceInput Capacitance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ Output Capacitance $f = 1.0 \text{ MHz}$	Gate-Body Leakage Current, Reverse $V_{GS} = -25 \text{ V}, V_{DS} = 0 \text{ V}$ racteristicsGate Threshold Voltage $V_{DS} = V_{GS}, I_D = 250 \mu \text{A}$ 2.0Static Drain-Source On-Resistance $V_{GS} = 10 \text{ V}, I_D = 5.0 \text{ A}$ Forward Transconductance $V_{DS} = 25 \text{ V}, I_D = 5.0 \text{ A}$ c Characteristics Input Capacitance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1.0 \text{ MHz}$	Gate-Body Leakage Current, Reverse $V_{GS} = -25 \text{ V}, V_{DS} = 0 \text{ V}$ racteristics Gate Threshold Voltage $V_{DS} = V_{GS}, I_D = 250 \mu \text{A}$ 2.0 Static Drain-Source On-Resistance $V_{GS} = 10 \text{ V}, I_D = 5.0 \text{ A}$ 0.11 Forward Transconductance $V_{DS} = 25 \text{ V}, I_D = 5.0 \text{ A}$ 4.9 c Characteristics Input Capacitance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1.0 \text{ MHz}$ 240	Gate-Body Leakage Current, Reverse $V_{GS} = -25 \text{ V}, V_{DS} = 0 \text{ V}$ 0.00 Gate Threshold Voltage $V_{DS} = V_{GS}, I_D = 250 \mu A$ 2.0 4.0 Static Drain-Source On-Resistance $V_{GS} = 10 \text{ V}, I_D = 5.0 \text{ A}$ 0.11 0.14











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FQD13N06 — N-Channel QFET[®] MOSFET



Rev. 166

Preliminary

No Identification Needed

Obsolete

First Production

Full Production

Not In Production

notice to improve design.

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